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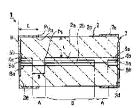
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(54) NTC THERMISTOR ELEMENT



(57)Abstract:

PROBLEM TO BE SOLVED: To lessen an irregularity in the resistance value of an NTC thermistor element and to make low the resistance of the thermistor element by method wherein first counter electrodes are arranged in such a way that at least each one part of the first opposed electrodes is superposed on internal electrodes, which are separated from each other via each thermistor layer and are respectively connected with potentials reverse to each other at

positions of different heights, in the thickness direction.

SOLUTION: An internal electrode consisting of first and second opposed electrodes 3a and 3b is formed at a position of a certain height and internal electrodes, which respectively consist of a first and second counter electrodes 4a and 4b, first and second counter electrodes 5a and 5b and first and second counter electrodes 6a and 7b, are formed under the lower part of the internal electrode consisting of the electrodes 3a and 3b. In the internal electrodes, the first counter electrodes 3a to 6a and the second counter electrodes 3b to 6b are arranged opposing to each other with each gap between them on the same plane. The electrode 3a is superposed on the electrode 4a of the internal electrode adjacent to the thickness direction with a ceramic layer 2a between them. The electrode 4a is superposed on the electrode 5a with a ceramic layer 2b between them. The electrode 5a is superposed on the electrode 6a with a ceramic layer 2c between them.

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CLAIMS

[Claim(s)]

[Claim 1] The thermistor element assembly which consists of an NTC thermistor ingredient, and two or more internal electrodes by which were separated and the laminating was carried out through the thermistor layer into said thermistor element assembly, In the 1st formed in the outside surface of said thermistor element assembly, and an NTC thermistor component equipped with the 2nd external electrode At least one internal electrode has a gap separated, and counters on the same flat surface. It has the 1st and 2nd counterelectrode by which each end was connected to one way each of the said 1st and 2nd external electrode. The NTC thermistor component characterized by being located so that said a part of 1st counterelectrode [at least] may lap in the 1st counterelectrode or internal electrode, and thickness direction which are connected to the opposite potential of a different height location separated through the thermistor layer. [Claim 2] The internal electrode which consists of said 1st and 2nd counterelectrode is said NTC thermistor component according to claim 1 arranged among the internal electrodes of a layer at both the maximum upper

layer, and lowest both [one side or]. [two or more]

[Claim 3] The NTC thermistor component according to claim 1 or 2 which has the 1st and 2nd counterelectrode with which all the internal electrodes had the gap separated, and countered on the same flat surface, and is located so that it may overlap in the 1st counterelectrode and thickness direction which are connected to the opposite potential of the height location where a part of each 1st counterelectrode [at least] has a thermistor layer separated in, and they differ. [Claim 4] An NTC thermistor component given in any of claims 1-3 which the 1st external electrode is formed in the 1st end face of a thermistor component, and the 2nd external electrode is formed in the 2nd end face of a thermistor component, and are arranged so that the counterelectrode connected to the 1st or 2nd external electrode may not lap with the 2nd or 1st external electrode in the thickness direction they are.

[Claim 5] An NTC thermistor component given in any of claims 1-4 by which distance of the 1st or 2nd external electrode and the internal electrode connected to the 2nd or 1st external electrode is made larger than the magnitude of said gap between the 1st of this internal electrode, and the 2nd counterelectrode in the internal electrode which has said 1st and 2nd counterelectrode they are. [Claim 6] The NTC thermistor component given in any of claims 1-5 they are carried out if the width of face of the 1st counterelectrode is other width of face and ** of an internal electrode which have been arranged so that it may overlap in the thickness direction through a thermistor component.

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DETAILED DESCRIPTION

[Detailed Description of the Invention] [0001]

[Field of the Invention] This invention relates to amelioration of the NTC thermistor component which comes to arrange two or more internal electrodes in a thermistor element assembly in a detail more about the NTC thermistor component which has a negative temperature coefficient of resistance.

[0002]

[Description of the Prior Art] The NTC thermistor component is broadly used, in order to detect the temperature of ambient temperature, a solid-state, a liquid, etc., or in order to compensate change of the circuit by temperature, or a components property.

[0003] Conventionally, the thing of the opposed type which comes to carry out opposite arrangement of the electrode on the same flat surface, and the laminating mold which comes to carry out the laminating of two or more internal electrodes to a list into a thermistor element assembly is known as a chip mold NTC thermistor component (Japanese Patent Application No. No. 250050 [two to], Japanese Patent Application No. No. 279913 [60 to], etc.). The structure of these NTC thermistor components is explained with reference to drawing 11 - drawing 13 R> 3.

[0004] Drawing 11 is the sectional view showing the conventional NTC thermistor component of an opposed type. The NTC thermistor component 61 has the thermistor element assembly 62 which consists of a sintered compact obtained using transition-metals element oxides, such as nickel oxide and cobalt oxide, two or more sorts. Into the thermistor element assembly 62, as an internal electrode, counterelectrodes 63 and 64 separate a predetermined gap and

opposite arrangement is carried out in a certain height location.

[0005] The external electrode 65 is formed in the one side end face of the thermistor element assembly 62, and the external electrode 66 is formed in the another side end face. The external electrode 65 is connected to a counterelectrode 63, and the external electrode 66 is connected to the counterelectrode 64. Resistance is determined with this NTC thermistor component 61 by the gap between a counterelectrode 63 and 64. Moreover, if counterelectrodes 63 and 64 are correctly formed on the green sheet used in case the thermistor element assembly 62 is obtained in order for what is necessary to be just to form counterelectrodes 63 and 64 on the same flat surface, resistance is controllable with high precision.

[0006] Drawing 12 is the sectional view showing other examples of the conventional opposed type NTC thermistor component. In addition to counterelectrodes 63 and 64, with the NTC thermistor component 67, Counterelectrodes 68a, 68b-70a and 70b are formed as two or more internal electrodes in the thermistor element assembly 62. That is, in four height locations, Counterelectrodes 63, 64-70a and 70b are formed [in the thermistor element assembly 62], respectively.

[0007] Drawing 13 is the sectional view showing the conventional laminating mold NTC thermistor component. The NTC thermistor component 71 has the structure arranged so that two or more internal electrodes 73-75 may be overlapped through a thermistor layer in the thermistor element assembly 72. Internal electrodes 73 and 75 are connected to the external electrode 76 of the thermistor element assembly 72 formed in the end face on the other hand. The internal electrode 74 is connected to the external electrode 77 formed in the another side end face of the thermistor element assembly 72.

[0008] With the NTC thermistor component 71, the NTC thermistor component 71 which resistance is determined between internal electrodes 73 and 75 and an internal electrode 74, therefore has small resistance can be offered.

[0009]

[Problem(s) to be Solved by the Invention] With the conventional opposed type NTC thermistor components 61 and 67, although resistance could be controlled with high precision, the limit was in low resistance-ization. That is, if width of face of the above-mentioned gap between a counterelectrode 63 and 64 or between Counterelectrodes 63, 64-70a and 70b is made small, although resistance can be made small, if the width of face of a gap becomes small, it will become easy to produce a short circuit. Therefore, it was difficult for a limit to be in low resistance-ization and for resistance to produce a small NTC thermistor component.

[0010] In addition, the problem of influencing not a little also had the dimension prolonged in the direction to which the both-ends side of the thermistor element assembly 62 of the external electrodes 65 and 66 is connected in the resistance acquired from the resistance between the external electrode 65 and 66 serving as Counterelectrodes 63, 64-70a, and 70b and parallel resistance.

[0011] On the other hand, there was a problem that resistance differed in the laminating mold NTC thermistor component 71 with the superposition precision of the green sheet with which thickness dispersion and the internal electrodes 73-75 of a green sheet for manufacture of what can achieve low resistance-ization by increasing the number of laminatings of internal electrodes 73-75 are formed etc. Therefore, although the NTC thermistor component of low resistance could be offered, the more it formed low resistance, the more dispersion in the resistance by the factor on the above-mentioned process had become a problem. The purpose of this invention has dispersion in resistance in offering the NTC thermistor component of low resistance few.

[0012]

[Means for Solving the Problem] The thermistor element assembly with which invention according to claim 1 consists of an NTC thermistor ingredient, In the NTC thermistor component which is separated through a thermistor layer in said thermistor element assembly, and is equipped with two or more internal electrodes by which the laminating was carried out, and the 1st and 2nd external

electrode formed at the outside surface of said thermistor element assembly At least one internal electrode has a gap separated, and counters on the same flat surface. It has the 1st and 2nd counterelectrode by which each end was connected to one way each of the said 1st and 2nd external electrode. Said a part of 1st counterelectrode [at least] is the NTC thermistor component characterized by being located so that it may lap in the 1st counterelectrode or internal electrode, and thickness direction which are connected to the opposite potential of a different height location separated through the thermistor layer. [0013] In invention according to claim 1, the internal electrode according to claim 2 which consists of the 1st and 2nd counterelectrode is preferably arranged among the internal electrodes of two or more layers like at both the maximum upper layer, and lowest both [one side or].

[0014] With the NTC thermistor component concerning invention according to claim 1 or 2, preferably, it has the 1st and 2nd counterelectrode according to claim 3 with which all the internal electrodes had the gap separated, and countered on the same flat surface like, and it is located so that it may overlap in the 1st counterelectrode and thickness direction which are connected to the opposite potential of the height location where a part of each 1st counterelectrode [at least] has a thermistor layer separated in, and they differ. [0015] In an NTC thermistor component [in / in invention according to claim 4 / invention given in any of claims 1-3 they are] The 1st external electrode is formed in the 1st end face of a thermistor component, and the 2nd external electrode is formed in the 2nd end face of a thermistor component. It is characterized by being arranged so that the counterelectrode connected to the 1st or 2nd external electrode may not lap with the 2nd or 1st external electrode in the thickness direction.

[0016] Moreover, the NTC thermistor component concerning invention according to claim 5 In the internal electrode which has said 1st and 2nd counterelectrode in an NTC thermistor component given in any of claims 1-4 they are Distance of the 1st or 2nd external electrode and the internal electrode connected to the 2nd

or 1st external electrode is characterized by being made larger than the magnitude of said gap between the 1st of this internal electrode, and the 2nd counterelectrode.

[0017] The NTC thermistor component concerning invention according to claim 6 is characterized by being carried out if the width of face of the 1st counterelectrode is other width of face and ** of an internal electrode which have been arranged so that it may overlap in the thickness direction through a thermistor component in an NTC thermistor component given in any of claims 1-5 they are.

[0018]

[Embodiment of the Invention] Hereafter, this invention is clarified by explaining the un-limiting-example of this invention, referring to a drawing.

[0019] (The 1st example) Drawing 1 is the sectional view of the NTC thermistor component concerning the 1st example of this invention. The NTC thermistor component 1 is constituted using the rectangular parallelepiped-like thermistor element assembly 2. The thermistor element assembly 2 is a sintered compact constituted using the oxide of transition-metals elements, such as nickel, cobalt, and copper, two or more sorts. The thermistor element assembly 2 is obtained by carrying out two or more sheet laminating of the ceramic green sheet with which the below-mentioned ceramic green sheet and below-mentioned internal electrode which come to form an internal electrode in a top face are not formed, and calcinating the obtained layered product.

[0020] In the thermistor element assembly 2, two or more internal electrodes which separate a predetermined gap and come to carry out opposite arrangement of the 1st and 2nd counterelectrode on the same flat surface are formed. That is, the internal electrode which consists of the 1st counterelectrode 3a and the 2nd counterelectrode 3b is formed in a certain height location, and each of that internal electrode that consists of the 1st counterelectrode 4a, the 2nd counterelectrode 4b, the 1st counterelectrode 5a, the 2nd counterelectrode 5b and the 1st counterelectrode 6a, and the 2nd counterelectrode 6b caudad,

respectively is formed.

[0021] In each internal electrode, on the same flat surface, the 1st counterelectrode 3a, 4a, 5a, and 6a and the 2nd counterelectrode 3b, 4b, 5b, and 6b separate a gap, and opposite arrangement is carried out. Therefore, the resistance determined in the opposite distance between the gap dimension g, i.e., the 1st, and 2nd counterelectrode can be kept highly precise if the 1st and 2nd counterelectrode 3a and 3b is formed by printing of conductive paste on a ceramic green sheet.

[0022] On the other hand, 1st counterelectrode 3a overlaps 1st counterelectrode 4a of the internal electrode which separates ceramic layer 2a and adjoins in the thickness direction. Similarly, 1st counterelectrode 4a also overlaps 1st downward counterelectrode 5a. Moreover, 1st counterelectrode 5a also overlaps 1st counterelectrode 6a of the lower part.

[0023] As mentioned above, since the 1st counterelectrode 3a-6a separates ceramic layer 2a, 2b, and 2c partially and laps, in the part shown with the notation B of drawing 1, resistance is taken out like a laminating mold thermistor component in these counterelectrodes 3a-6a.

[0024] Therefore, in the NTC thermistor component 1, when attaining low resistance-ization, resistance can be made small by increasing the number of laminatings of the 1st counterelectrode 3a-6a. Moreover, in the opposed type part shown by A as mentioned above, although resistance is taken out by the gap, since this gap dimension g can be controlled with high precision, it can reduce dispersion in resistance.

[0025] That is, the small NTC thermistor component 1 of dispersion in resistance may be offered small [resistance] by combining the structure of the conventional opposed type NTC thermistor component, and the structure of a laminating mold NTC thermistor component.

[0026] On the occasion of manufacture of the NTC thermistor component 1, the ceramic green sheet of two or more sheets which consists of a thermistor ingredient which functions as an NTC thermistor is prepared. A perspective view

shows some of these ceramic green sheets to drawing 2.

[0027] As for the electrode, the flat-surface configuration is not printed by the top face of rectangular ceramic green sheet 9a. In order to form the 1st counterelectrode 3a and 2nd counterelectrode 3b on ceramic green sheet 9b, Ag-Pd powder content conductive paste is printed corresponding to these counterelectrodes 3a and 3b. Similarly, on ceramic green sheet 9c and 9d, the 1st Counterelectrodes 4a and 5a and 2nd counterelectrode 4b and 5b are printed. In addition, although not illustrated in drawing 2, it is printed on the same ceramic green sheet also about the counterelectrodes 6a and 6b shown in drawing 1.

[0028] Next, as shown in drawing 3, a laminating is carried out and the thermistor element assembly 2 is obtained for the ceramic green sheets 9a, 9b, and 9c of two or more sheets, and 9d.... by really calcinating. In this case, ceramic green sheet 9a by which the internal electrode shown in drawing 2 is not printed is used the proper number of sheets in the upper part of the thermistor element assembly 2, and a lower part.

[0029] Next, the 2nd external electrode 8 is formed so that the 2d of the 1st end face of the thermistor element assembly 2 of drawing 1 may be covered and 2nd end-face 2e may be covered for the 1st external electrode 7. Formation of the external electrodes 7 and 8 applies conductive powder content conductive paste like Ag, and is performed by the ability being burned. In this case, the 1st and 2nd external electrode 7 and 8 is formed so that not only the end faces 2d and 2e of the thermistor element assembly 2 but the top face, inferior surface of tongue, and both-sides side to which end faces 2d and 2e are connected may be reached. In drawing 1, the part which has reached the top face and inferior surface of tongue of the external electrodes 7 and 8 is illustrated. Besides, hereafter, an external electrode wears the part which has reached the both-sides side at the field and the inferior-surface-of-tongue list, and let them be Sections 7a and 8a.

[0030] The 1st Counterelectrodes 3a and 5a and 2nd counterelectrode 4b and 6b

are connected to the 1st external electrode 7, and the 1st Counterelectrodes 4a and 6a and 2nd counterelectrode 3b and 5b are electrically connected to the 2nd external electrode 8.

[0031] In addition, the 1st counterelectrode 3a, 4a, and 5a consists of drawing 2 so that it may have equal width of face altogether. In addition, the width of face of the 1st counterelectrode shall mean the dimension of the 1st counterelectrode of the direction to which the both-ends sides 2d and 2e of the thermistor element assembly 2 are connected, and the direction which intersects perpendicularly here.

[0032] On the other hand, dispersion in the resistance acquired can be further reduced by changing more preferably the width of face of the 1st counterelectrode which overlaps through a thermistor layer. That is, as shown in drawing 4 (a) and (b), when width of face of 1st counterelectrode 5a is made larger than the width of face of 1st counterelectrode 6a which overlaps 1st counterelectrode 5a through a thermistor layer, dispersion in the resistance resulting from the laminating gap in the cross direction can be reduced. That is, since the lap area between the 1st counterelectrode 5a and 6a is not changed as long as 1st counterelectrode 6a is located in the field which projected 1st counterelectrode 5a caudad even if it is the case where a printing gap and a laminating gap arise crosswise on the occasion of printing of a laminating or Counterelectrodes 5a and 6a, dispersion in the resistance resulting from the above-mentioned printing gap or a laminating gap can be prevented. [0033] Moreover, the connection three a1 which results in full [of a ceramic green sheet] in formation of the 1st and 2nd counterelectrode 3a and 3b in the part which stands in a row in the edge of ceramic green sheet 9b as shown in drawing 5 (a) and three b1 You may prepare. Thus, a connection three a1 and three b1 By preparing, the dependability of electrical installation with the external electrodes 7 and 8 of the 1st and 2nd counterelectrode 3a and 3b can be raised. And since, as for a part for the principal part of the 1st and 2nd counterelectrode 3a and 3b, width of face is narrowed rather than ceramic green sheet 9b,

moisture resistance is also raised.

[0034] Furthermore, the electrode finger three a2 which the 1st and 2nd counterelectrode 3a and 3b puts in a tip side mutually in between as shown in drawing 5 (b) and three b2 It is good also as the shape of a sinking comb which it has. Thus, low resistance-ization can be further attained by making the 1st and 2nd counterelectrode 3a and 3b counter in the shape of a sinking comb. [0035] Next, based on the concrete example of an experiment, according to the NTC thermistor component of the 1st example, even when low resistance-ization is attained, it is shown that dispersion in resistance can be reduced. Since the thermistor element assembly 2 was constituted, the ceramic green sheet of two or more sheets which makes the oxide of Mn, nickel, and Co a subject was prepared, and the 1st and 2nd counterelectrode 3a, 3b-6a and the ceramic green sheet which comes to print 6b, respectively were produced on the top face. The laminating of the ceramic green sheets 9a-9d (drawing 3) with which the 1st and 2nd counterelectrode was printed was carried out, and the laminating of the ceramic green sheet 9a of the proper number of sheets which is not printing the counterelectrode further was carried out up and down.

[0036] The external electrodes 7 and 8 were formed by calcinating the layered product obtained as mentioned above, applying the electrode which consists of Ag to the obtained thermistor element assembly, and being burned on it. Various the numbers of laminatings of the internal electrode which produces the NTC thermistor component of the 1st example as mentioned above, and consists of the 1st and 2nd counterelectrode were changed, and various NTC thermistor components according to the 1st example were produced. Moreover, the resistance and resistance dispersion of an NTC thermistor component which were acquired by doing in this way were evaluated. A result is shown in the following table 1.

[0037] For the comparison, the same ingredient as the NTC thermistor component of the above-mentioned example was used, and the conventional opposed type NTC thermistor component 67 of this dimension and the laminating

mold NTC thermistor component 71 were produced. Also in this conventional opposed type NTC thermistor component 67 and the laminating mold NTC thermistor component 71, the number of laminatings of an internal electrode was changed, and what has the internal electrode of various number of sheets was produced, and resistance and resistance dispersion were evaluated. A result is collectively shown in the following table 1.

[0038]

[Table 1]

to a state has			比 較 例						
有	第1の実施例			対 向 型			積 層 型		
積層数	抵抗値R [kΩ]	抵抗 ばらつき R _{acv} [約]	積層数	抵抗値R [kΩ]	抵抗 ばらつき R s c v[%]	積層数	抵抗値R [kΩ]	抵抗 ばらつき R s cv[k]	
2	1. 30	6	1	5. 8	7	2	1. 59	2 5	
3	0.62	5	3	3. 6	6	3	0.78	1 8	
4	0.41	4	5	2. 5	5	4	0.50	1.5	
6	0. 25	3. 6				5	0.32	1 5	
9	0.15	3. 4				10	0.16	15	

[0039] Since resistance is determined by the gap with an opposed type NTC thermistor component so that clearly from Table 1, it is resistance dispersion R3valve flow coefficient. It can be made small. On the other hand, at a laminating mold NTC thermistor component, it is resistance dispersion R3valve flow coefficient by various factors, such as a laminating gap of an internal electrode, a printing gap, and a cutting gap from a mother's ceramic green sheet. It turns out that it is very large.

[0040] Moreover, with the NTC thermistor component produced according to the 1st example, if the number of laminatings of an internal electrode is the same, it turns out that an NTC thermistor component with very small resistance can be offered compared with an opposed type NTC thermistor component, so that clearly from Table 1.

[0041] In addition, with an opposed type NTC thermistor component, although low resistance-ization can be attained by increasing the number of internal

electrodes, in order to lower less than [1kohm] and resistance, it turns out that the laminating of most number of the internal electrodes must be carried out, therefore a thickness dimension increases.

[0042] Moreover, in the NTC thermistor component concerning the 1st example, various the number of the internal electrodes which consist of the 1st and 2nd counterelectrode is changed, and it is resistance and resistance dispersion R3valve flow coefficient. It measured. A result is shown in drawing 6 and drawing 7.

[0043] According to this invention, by increasing the number of sheets of an internal electrode shows that resistance may be reduced remarkably so that clearly from drawing 6 and drawing 7. Therefore, by fluctuating the number of the internal electrodes which have the 1st and 2nd counterelectrode according to an application shows that the NTC thermistor component of especially low resistance which has desired resistance can be manufactured with high precision. [0044] The 1st and 2nd external electrode 7 and 8 wears, preferably, Sections 7a and 8a consist of NTC thermistor components 1 of the 1st example so that it may not overlap in the counterelectrode connected to lower part potential, and the thickness direction, and dispersion in resistance is further reduced by it. This is explained with reference to drawing 1 and drawing 8.

[0045] In the NTC thermistor component 1, the 2nd external electrode 8 wears, and as shown in drawing 1, section 8a is arranged so that 1st counterelectrode 3a connected to another side potential may not be overlapped in the thickness direction. this structure -- setting -- wearing -- from the outside surface on endface 2e of die-length [of section 8a] L8, i.e., the 2nd external electrode, -- wearing -- tip P1 of section 8a up to -- the horizontal distance of the tip of section 8a and 1st counterelectrode 3a is changed, as it wears in distance and a list and is shown in the following table 2 -- making -- resistance R and dispersion R3valve flow coefficient of resistance And resistance rate of change was evaluated. In addition, resistance rate of change is a value on the basis of the case where the above-mentioned lap die length is -0.2mm.

[0046] Moreover, the NTC thermistor component 11 to which it wears and section 8a overlaps 1st counterelectrode 3a by die length of X= +0.1mm in the thickness direction for the comparison as shown in drawing 8 is produced, and they are resistance R and resistance dispersion R3valve flow coefficient similarly. It measured and resistance rate of change was evaluated. A result is collectively shown in Table 2.

[0047]

[Table 2]

L [1010]	抵抗値R [kΩ]	ばらつき		抵抗変化率 AR [%]	
0. 2	0.410	5	-0,2↑重		
0.3	0.410	5	- 0. 1 らな	0	
0.4	0.409	5. 2	0 (1)	-0.02	
0. 5	0.403	7	+0.1 ^重 なる	-1.8	

[0048] With the NTC thermistor component 11 shown in drawing 8, it turns out that the external electrode 8 wears, and it changes a lot compared with the case where resistance does not overlap since section 8a overlaps 1st counterelectrode 3a connected to another side potential in the thickness direction so that clearly from Table 2. When in other words counterelectrode 3a of the external electrode 8 to wear and by which section 8a is connected to another side potential is overlapped in the thickness direction, and the die-length dimension of this ****-ed 8a varies, it turns out that resistance varies greatly. [0049] Therefore, they are resistance R and resistance dispersion R3valve flow coefficient as mentioned above preferably by the external electrode's 8 wearing, and arranging section 8a so that it may not overlap in counterelectrode 3a and the thickness direction in which it connects with another side potential. It turns out that it can decrease further.

[0050] Moreover, the external electrode 8 wears with the NTC thermistor component 1 of the 1st example, and it is the tip P1 of section 8a. Tip P2 of

counterelectrode 3a connected to another side potential The distance of a between found out influencing dispersion in resistance. Preferably, it sets to this invention and is the above P1 and P2. It is made larger than the dimension g of the gap between 1st counterelectrode 3a of the same internal electrode, and 2nd counterelectrode 3b, and the distance of a between is resistance dispersion R3valve flow coefficient by it. Reduction can be achieved.

[0051] The dimension g of a gap is set to 0.25mm in the NTC thermistor component 1 of the 1st example. The 2nd external electrode 8 wears and the die-length dimension of 0.3mm and 2nd counterelectrode 3b is set to 0.05mm for die-length L of section 8a. It is P1 and P2 by changing thickness t (referring to drawing 1) of the thermistor layer between counterelectrode 3a and the top face of the thermistor element assembly 2, as shown in the following table 3. The distance of a between was changed and dispersion in resistance was evaluated. A result is shown in the following table 3.

[0052]

[Table 3]

厚み t [.uua]	P ₁ とP ₂ との 距離p [mm]	抵抗 ばらつき R _{scv} [約]	
0.8	0. 28	4. 0	
0.75	0.255	4. 2	
0.70	0.230	5. 8	
0.65	0.205	8. 1	

[0053] It is P1 and P2 so that clearly from Table 3. When the distance of a between is larger than the gap length dimension g, it is resistance dispersion R3valve flow coefficient. It turns out that it can be made small.

[0054] (The 2nd example) Drawing 9 is the sectional view showing the NTC thermistor component concerning the 2nd example of this invention.

[0055] The internal electrode of four layers consists of NTC thermistor components 31 in the rectangular parallelepiped-like thermistor element assembly 2. But the internal electrodes 32 and 33 located in the center of the

thickness direction are connected to the 1st and 2nd external electrode 7 and 8, respectively. That is, it replaces with the 1st and 2nd counterelectrode 4a, 4b, 5a, and 5b of the NTC thermistor component 1 shown in drawing 1, and the above-mentioned internal electrodes 32 and 33 are used. About other points, since it is the same as that of the NTC thermistor component 1, it omits [part / same] by using explanation of the 1st example by ****** which attaches the same reference number.

[0056] Like the NTC thermistor component 31, there is not necessarily no need that all internal electrodes are formed with the 1st and 2nd counterelectrode, and it may combine the internal electrode connected to the 1st or 2nd external electrode by turns like the case of the conventional laminating mold NTC thermistor component in addition to the internal electrode which consists of the 1st and 2nd counterelectrode the proper number of sheets.

[0057] Also in this case, in the above-mentioned laminating mold NTC thermistor section, reduction of resistance can be aimed at according to increase of the number of laminatings in the part and list which can control dispersion in resistance with high precision with a gap g, and are constituted like an opposed type NTC thermistor component with the 1st counterelectrode, the 1st counterelectrode of other height locations, or an internal electrode.

[0058] Therefore, like the NTC thermistor component 31, the 1st and 2nd counterelectrode and the internal electrode of a laminating mold NTC thermistor component can be combined suitably, and it is arbitrary also about the combination direction.

[0059] But it is desirable like [it is desirable and] the NTC thermistor component 31 to arrange the 1st and 2nd counterelectrode 3a, 3b, 6a, and 6b in the thickness direction outermost layer. With the internal electrode of a laminating mold NTC thermistor component, and the internal electrodes 32 and 33 constituted similarly, it is hard to produce dispersion in the resistance by such cause to dispersion in resistance arising with the distance between the tip and the external electrodes 8 or 7 connected to another side potential in the opposed

type internal electrodes 3a, 3b, 6a, and 6b.

[0060] (The 3rd example) Drawing 10 is the sectional view showing the NTC thermistor component concerning the 3rd example of this invention. The NTC thermistor component 41 has the configuration which has arranged the two-layer internal electrode in the thermistor element assembly 2, and each internal electrode has the 1st and 2nd counterelectrode, respectively. That is, the 1st counterelectrode 42a and 2nd counterelectrode 42b are formed up, and 1st counterelectrode 43a and 2nd counterelectrode 43b are formed caudad. Moreover, Counterelectrodes 42a and 43b are connected to the 1st external electrode 7, and Counterelectrodes 42b and 43a are connected to the 2nd external electrode 8. Therefore, since it not only can achieve reduction of resistance dispersion, but 1st counterelectrode 42a and 1st counterelectrode 43a overlap through the thermistor layer like the NTC thermistor component of the 1st example, low resistance-ization can also be achieved. That is, the NTC thermistor component 41 is equivalent to the example by which the NTC thermistor component of this invention was simplified most.

[0061]

[Effect of the Invention] According to invention according to claim 1, it has the 1st and 2nd counterelectrode with which at least one internal electrode separated the gap, and countered in the same flat surface. Since a part of 1st counterelectrode [at least] is arranged so that it may overlap in the internal electrode connected to the opposite potential of a different height location separated through the thermistor layer, and the thickness direction, It not only can reduce dispersion in resistance like the conventional opposed type NTC thermistor component, but it can aim at reduction of resistance like the conventional laminating mold NTC thermistor component by the lap of the 1st counterelectrode of the above, and other internal electrodes. [0062] Therefore, since it is possible to become possible to offer the NTC thermistor component of low resistance with high precision, and to aim at

reduction of resistance and its dispersion according to electrode structure, the

resistance of the large range can be acquired using the thermistor ingredient of the same B constant. Since in other words the NTC thermistor component of various resistance can be supplied using the same NTC thermistor ingredient for resistance, the degree of freedom on the circuit design by the side of a user can be raised effectively.

[0063] According to invention according to claim 2, since the internal electrode which consists of the 1st and 2nd counterelectrode is arranged among the internal electrodes of two or more layers at both the maximum upper layer, and lowest both [one side or], it is hard to produce dispersion in the resistance by the distance between the external electrodes connected to another side potential. [0064] According to invention according to claim 3, since all internal electrodes are constituted so that it may have the 1st and 2nd counterelectrode of the above, they become possible [reducing dispersion in resistance further].

[0065] Since according to invention according to claim 4 it is arranged so that the counterelectrode connected to the 1st or 2nd external electrode may not lap with the 2nd or 1st external electrode in the thickness direction, dispersion in the resistance by the distance between these can be reduced, and dispersion in resistance can be reduced further.

[0066] According to invention according to claim 5, since distance between the 1st or 2nd external electrode and the internal electrode connected to the 2nd or 1st external electrode is made larger than the magnitude of the gap between the 1st of this internal electrode, and the 2nd counterelectrode, it becomes possible [reducing dispersion in resistance further].

[0067] In invention according to claim 6, since it is carried out if the width of face of the 1st counterelectrode is the width of face and ** of an internal electrode which were separated through the thermistor layer, it becomes possible to reduce effectively dispersion in the resistance resulting from the laminating gap of the cross direction and the printing gap of an electrode in a production process.

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DESCRIPTION OF DRAWINGS

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[Brief Description of the Drawings]

[Drawing 1] The sectional view showing the NTC thermistor component concerning the 1st example of this invention.

[Drawing 2] The decomposition perspective view showing the ceramic green sheet used in the production process of the NTC thermistor component of the 1st example, and an electrode configuration.

[Drawing 3] The schematic-drawing-perspective view for explaining the process which carries out the laminating of the ceramic green sheet of two or more sheets in the production process of the NTC thermistor component of the 1st example.

[Drawing 4] (a) And (b) is each top view for explaining the structure where the width of face of a counterelectrode was changed.

[Drawing 5] (a) And (b) is each perspective view for explaining the modification of the flat-surface configuration of a counterelectrode.

[Drawing 6] Drawing showing the relation between the number of laminatings of an internal electrode, and resistance in the NTC thermistor component of the 1st example.

[Drawing 7] It sets for the NTC thermistor component of the 1st example, and is dispersion R3valve flow coefficient of the number of laminatings of an internal

electrode, and resistance. Drawing showing relation.

[Drawing 8] The sectional view for explaining the structure prepared for the comparison in which ****-ed [external electrode] overlaps the counterelectrode in the thickness direction.

[Drawing 9] The sectional view showing the NTC thermistor component concerning the 2nd example of this invention.

[Drawing 10] The sectional view showing the NTC thermistor component concerning the 3rd example of this invention.

[Drawing 11] The sectional view showing an example of the conventional opposed type NTC thermistor component.

[Drawing 12] The sectional view showing other examples of the conventional opposed type NTC thermistor component.

[Drawing 13] The sectional view showing the conventional laminating mold NTC thermistor component.

[Description of Notations]

1 -- NTC thermistor component

2 -- Thermistor element assembly

2a-2c -- Thermistor layer

2d, 2e -- End face

3a, 4a, 5a, 6a -- The 1st counterelectrode

3b, 4b, 5b, 6b -- The 2nd counterelectrode

7 8 -- The 1st, 2nd external electrode

7a, 8a -- An external electrode wears and it is the section.

31 -- NTC thermistor component

32 33 -- Internal electrode

41 -- NTC thermistor component

42a, 43a -- The 1st counterelectrode

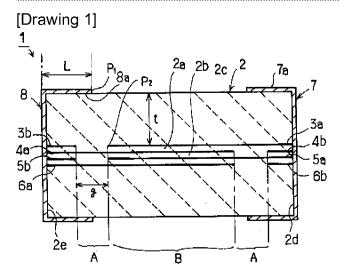
42b, 43b -- The 2nd counterelectrode

* NOTICES *

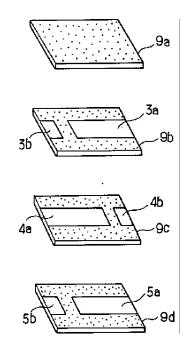
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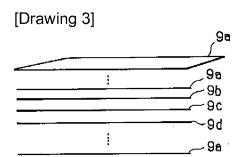
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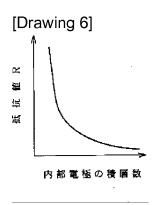
DRAWINGS



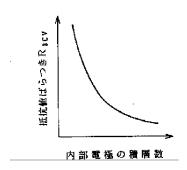
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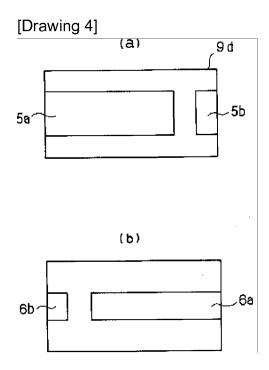




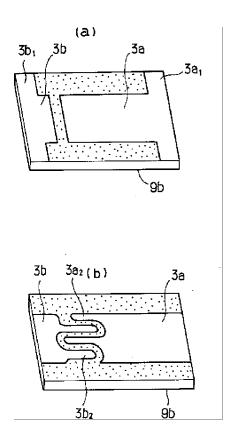


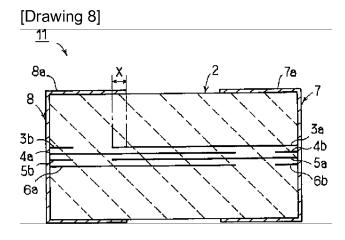
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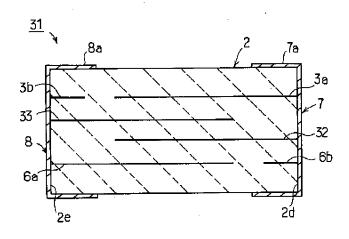


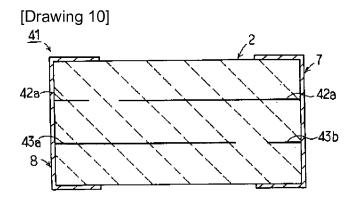
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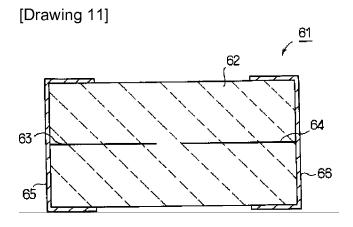




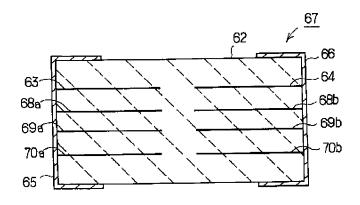
[Drawing 9]



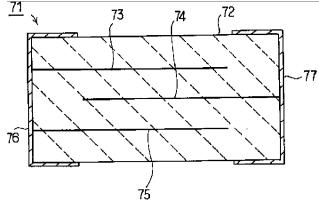




[Drawing 12]



[Drawing 13] 71



[Translation done.]

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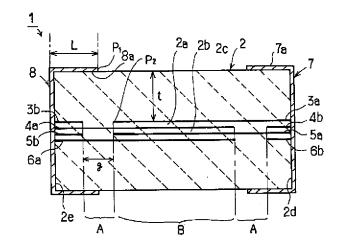
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(54) 【発明の名称】 NTCサーミスタ素子

(57)【要約】

【課題】 低抵抗であり、かつ抵抗値のばらつきの少な いNTCサーミスタ素子を得る。

【解決手段】 少なくとも1つの内部電極が、ギャップ を隔てて同一平面上において対向配置された第1,第2 の対向電極3a, 3bを有し、第1の対向電極3aの少 なくとも一部がサーミスタ層を介して異なる高さ位置の 反対電位に接続される内部電極の第1の対向電極4aに 厚み方向に重なり合うように構成されているサーミスタ 素体2を有し、サーミスタ素体2の両端面に外部電極 7,8が形成されているNTCサーミスタ素子1。



【特許請求の範囲】

【請求項1】 NTCサーミスタ材料よりなるサーミスタ素体と、

前記サーミスタ素体内においてサーミスタ層を介して隔 てられて積層された複数の内部電極と、

前記サーミスタ素体の外表面に形成された第1,第2の外部電極とを備えるNTCサーミスタ素子において、 少なくとも1つの内部電極が、ギャップを隔てられて同一平面上で対向され、それぞれの一端が前記第1,第2の外部電極の各一方に接続された第1,第2の対向電極を有し

前記第1の対向電極の少なくとも一部が、サーミスタ層を介して隔てられた異なる高さ位置の反対電位に接続される第1の対向電極もしくは内部電極と厚み方向に重なるように位置されていることを特徴とする、NTCサーミスタ素子。

【請求項2】 前記第1,第2の対向電極からなる内部 電極が、前記複数層の内部電極のうち最上層と最下層の 一方または両方に配置されている、請求項1に記載のN TCサーミスタ素子。

【請求項3】 全ての内部電極がギャップを隔てられて同一平面上で対向された第1,第2の対向電極を有し、各第1の対向電極の少なくとも一部がサーミスタ層を隔てられて異なる高さ位置の反対電位に接続される第1の対向電極と厚み方向に重なり合うように位置されている、請求項1または2に記載のNTCサーミスタ素子。

【請求項4】 第1の外部電極がサーミスタ素子の第1 の端面に、第2の外部電極がサーミスタ素子の第2の端面に形成されており、第1または第2の外部電極に接続された対向電極が、第2または第1の外部電極と厚み方向において重ならないように配置されている、請求項1~3の何れかに記載のNTCサーミスタ素子。

【請求項5】 前記第1,第2の対向電極を有する内部電極において、第1または第2の外部電極と、第2または第1の外部電極に接続された内部電極との距離が、該内部電極の第1,第2の対向電極間の前記ギャップの大きさよりも大きくされている、請求項1~4の何れかに記載のNTCサーミスタ素子。

【請求項6】 第1の対向電極の幅が、サーミスタ素子を介して厚み方向に重なり合うように配置された他の内部電極の幅と異ならされている、請求項1~5の何れかに記載のNTCサーミスタ素子。

【発明の詳細な説明】

[0001]

【発明の属する技術分野】本発明は、負の抵抗温度係数を有するNTCサーミスタ素子に関し、より詳細には、サーミスタ素体内に複数の内部電極を配置してなるNTCサーミスタ素子の改良に関する。

[0002]

【従来の技術】NTCサーミスタ素子は、雰囲気温度、

固体や液体等の温度を検出するため、あるいは温度による回路や部品特性の変化を補償するために幅広く用いられている。

【0003】従来、チップ型NTCサーミスタ素子として、電極を同一平面上において対向配置してなる対向型、並びに複数の内部電極をサーミスタ素体内において積層してなる積層型のものが知られている(特願平2-250050号、特願昭60-279913号など)。これらのNTCサーミスタ素子の構造を、図11~図13を参照して説明する。

【0004】図11は、対向型の従来のNTCサーミスタ素子を示す断面図である。NTCサーミスタ素子61は、例えば酸化ニッケルや酸化コバルトなどの遷移金属元素酸化物を複数種用いて得られた焼結体からなるサーミスタ素体62を有する。サーミスタ素体62内には、ある高さ位置に、内部電極として対向電極63,64が所定のギャップを隔てて対向配置されている。

【0005】サーミスタ素体62の一方端面には外部電極65が、他方端面には外部電極66が形成されている。外部電極65は対向電極63に、外部電極66は対向電極64に接続されている。このNTCサーミスタ素子61では、対向電極63,64間のギャップにより抵抗値が決定される。また、同一平面上に対向電極63,64を形成すればよいため、サーミスタ素体62を得る際に用いられるグリーンシート上において正確に対向電極63,64を形成すれば、抵抗値を高精度に制御することができる。

【0006】図12は、従来の対向型NTCサーミスタ素子の他の例を示す断面図である。NTCサーミスタ素子67では、サーミスタ素体62内に、複数の内部電極として、対向電極63,64に加えて、対向電極68a,68b~70a,70bが形成されている。すなわち、サーミスタ素体62内において4つの高さ位置において、それぞれ、対向電極63,64~70a,70bが形成されている。

【0007】図13は、従来の積層型NTCサーミスタ素子を示す断面図である。NTCサーミスタ素子71は、サーミスタ素体72内に、複数の内部電極73~75をサーミスタ層を介して重なり合うように配置した構造を有する。内部電極73、75はサーミスタ素体72の一方端面に形成された外部電極76に接続されている。内部電極74はサーミスタ素体72の他方端面に形成された外部電極77に接続されている。

【0008】NTCサーミスタ素子71では、内部電極73,75と内部電極74との間で抵抗値が決定され、従って小さな抵抗値を有するNTCサーミスタ素子71を提供することができる。

[0009]

【発明が解決しようとする課題】従来の対向型NTCサーミスタ素子61,67では、抵抗値を高精度にコント

ロールし得るものの、低抵抗化に限度があった。すなわち、対向電極63,64間、あるいは対向電極63,64 \sim 70 α ,70 β 0間の上記ギャップの幅を小さくすれば抵抗値を小さくし得るものの、ギャップの幅が小さくなると短絡が生じ易くなる。従って、低抵抗化に限度があり、抵抗値が小さなNTCサーミスタ素子を作製することが困難であった。

【0010】加えて、外部電極65,66のサーミスタ素体62の両端面を結ぶ方向に延びる寸法が、外部電極65,66間の抵抗値が対向電極63,64~70a,70bと並列抵抗となることより、得られる抵抗値に少なからず影響するという問題もあった。

【0011】他方、積層型NTCサーミスタ素子71では、内部電極73~75の積層数を増大させることにより低抵抗化を果たすことができるものの、製造に際してのグリーンシートの厚みばらつき及び内部電極73~75が形成されているグリーンシートの重ね合わせ精度などによって、抵抗値がばらつくという問題があった。従って、低抵抗のNTCサーミスタ素子を提供し得るものの、低抵抗化すればする程上記工程上の要因による抵抗値のばらつきが問題となっていた。本発明の目的は、抵抗値のばらつきが少なく、かつ低抵抗のNTCサーミスタ素子を提供することにある。

[0012]

【課題を解決するための手段】請求項1に記載の発明は、NTCサーミスタ材料よりなるサーミスタ素体と、前記サーミスタ素体内においてサーミスタ層を介して隔てられて積層された複数の内部電極と、前記サーミスタ素体の外表面に形成された第1,第2の外部電極とを備えるNTCサーミスタ素子において、少なくとも1つの内部電極が、ギャップを隔てられて同一平面上で対向され、それぞれの一端が前記第1,第2の外部電極の各一方に接続された第1,第2の対向電極を有し、前記第1の対向電極の少なくとも一部が、サーミスタ層を介して隔てられた異なる高さ位置の反対電位に接続される第1の対向電極もしくは内部電極と厚み方向に重なるように位置されていることを特徴とする、NTCサーミスタ素子である。

【0013】請求項1に記載の発明では、好ましくは、 請求項2に記載のように、第1,第2の対向電極からな る内部電極が、複数層の内部電極のうち最上層と最下層 の一方または両方に配置されている。

【0014】請求項1または2に記載の発明に係るNT Cサーミスタ素子では、好ましくは、請求項3に記載のように、全ての内部電極がギャップを隔てられて同一平 面上で対向された第1,第2の対向電極を有し、各第1 の対向電極の少なくとも一部がサーミスタ層を隔てられて異なる高さ位置の反対電位に接続される第1の対向電極と厚み方向に重なり合うように位置されている。

【0015】請求項4に記載の発明は、請求項1~3の

何れかに記載の発明におけるNTCサーミスタ素子において、第1の外部電極がサーミスタ素子の第1の端面に、第2の外部電極がサーミスタ素子の第2の端面に形成されており、第1または第2の外部電極に接続された対向電極が、第2または第1の外部電極と厚み方向において重ならないように配置されていることを特徴とする。

【0016】また、請求項5に記載の発明に係るNTC サーミスタ素子は、請求項1~4の何れかに記載のNT Cサーミスタ素子において、前記第1,第2の対向電極 を有する内部電極において、第1または第2の外部電極 と、第2または第1の外部電極に接続された内部電極と の距離が、該内部電極の第1,第2の対向電極間の前記 ギャップの大きさよりも大きくされていることを特徴と する。

【0017】請求項6に記載の発明に係るNTCサーミスタ素子は、請求項1~5の何れかに記載のNTCサーミスタ素子において、第1の対向電極の幅が、サーミスタ素子を介して厚み方向に重なり合うように配置された他の内部電極の幅と異ならされていることを特徴とする。

[0018]

【発明の実施の形態】以下、図面を参照しつつ本発明の 非限定的な実施例を説明することにより、本発明を明ら かにする。

【0019】(第1の実施例)図1は、本発明の第1の実施例に係るNTCサーミスタ素子の断面図である。NTCサーミスタ素子1は、直方体状のサーミスタ素体2を用いて構成されている。サーミスタ素体2は、例えば、ニッケル、コバルト、銅などの遷移金属元素の酸化物を複数種用いて構成された焼結体である。サーミスタ素体2は、後述の内部電極を上面に形成してなるセラミックグリーンシート及び内部電極が形成されていないセラミックグリーンシートを複数枚積層し、得られた積層体を焼成することにより得られる。

【0020】サーミスタ素体2内には、第1,第2の対向電極を同一平面上において所定のギャップを隔てて対向配置してなる複数の内部電極が形成されている。すなわち、ある高さ位置に、第1の対向電極3aと、第2の対向電極3bとからなる内部電極が形成されており、その下方に、それぞれ、第1の対向電極4a,第2の対向電極4b、第1の対向電極5a,第2の対向電極5b及び第1の対向電極6a,第2の対向電極6bからなる各内部電極が形成されている。

【0021】各内部電極においては、第1の対向電極3 a,4a,5a,6aと、第2の対向電極3b,4b, 5b,6bとが同一平面上においてギャップを隔てて対 向配置されている。従って、ギャップ寸法g、すなわち 第1,第2の対向電極間の対向距離で決定される抵抗値 は、セラミックグリーンシート上に、例えば第1,第2 の対向電極3a, 3bを導電ペーストの印刷により形成 すれば、高精度に保ち得る。

【0022】他方、第1の対向電極3aは、セラミック層2aを隔てて厚み方向に隣接する内部電極の第1の対向電極4aと重なり合っている。同様に、第1の対向電極4aは、下方の第1の対向電極5aにも重なり合っている。また、第1の対向電極5aは、その下方の第1の対向電極6aにも重なり合っている。

【0023】上記のように、第100対向電極 $3a\sim6a$ が部分的にセラミック層2a, 2b, 2cを隔てて重なり合わされているため、図10記号Bで示す部分においては、この対向電極 $3a\sim6a$ において積層型サーミスタ素子と同様にして抵抗が取り出される。

【0024】よって、NTCサーミスタ素子1において、低抵抗化を図る場合、第1の対向電極3a~6aの積層数を増大させることにより、抵抗値を小さくすることができる。また、上記のようにAで示す対向型部分では、ギャップにより抵抗値が取り出されるが、このギャップ寸法gは高精度に制御し得るため、抵抗値のばらつきを低減し得る。

【0025】すなわち、従来の対向型NTCサーミスタ素子の構造と、積層型NTCサーミスタ素子の構造とを組み合わせることにより、抵抗値が小さく、かつ抵抗値のばらつきの小さなNTCサーミスタ素子1が提供され得る。

【0026】NTCサーミスタ素子1の製造に際しては、NTCサーミスタとして機能するサーミスタ材料よりなる複数枚のセラミックグリーンシートを用意する。これらのセラミックグリーンシートの一部を図2に斜視図で示す。

【0027】平面形状が矩形のセラミックグリーンシート9aの上面には、電極は印刷されていない。セラミックグリーンシート9b上には、第1の対向電極3a及び第2の対向電極3bを形成するために、該対向電極3a,3bに応じて例えばAg-Pd粉末含有導電ペーストが印刷されている。同様に、セラミックグリーンシート9c,9d上には、第1の対向電極4a,5a及び第2の対向電極4b,5bが印刷されている。なお、図2では図示していないが、図1に示した対向電極6a,6bについても、同様のセラミックグリーンシート上に印刷される。

【0028】次に、図3に示すように、複数枚のセラミックグリーンシート9a,9b,9c,9d……を積層し、一体焼成することによりサーミスタ素体2を得る。この場合、図2に示した内部電極の印刷されていないセラミックグリーンシート9aは、サーミスタ素体2の上方及び下方において適宜の枚数用いられる。

【0029】次に、図1のサーミスタ素体2の第1の端面2dを覆うように第1の外部電極7を、第2の端面2eを覆うように第2の外部電極8を形成する。外部電極

7,8の形成は、例えば、Agのような導電性粉末含有 導電ペーストを塗布し、焼き付けることにより行われ る。この場合、第1,第2の外部電極7,8は、サーミ スタ素体2の端面2d,2eだけでなく、端面2d,2 eを結んでいる上面、下面及び両側面にも至るように形 成される。図1では、外部電極7,8の上面及び下面に 至っている部分が図示されている。この上面及び下面並 びに両側面に至っている部分を以下、外部電極の被り部 7a,8aとする。

【0030】第1の対向電極3a,5a及び第2の対向電極4b,6bが第1の外部電極7に接続されており、第1の対向電極4a,6a及び第2の対向電極3b,5bが第2の外部電極8に電気的に接続されている。

【0031】なお、図2では、第1の対向電極3a,4a,5aは、全て等しい幅を有するように構成されている。なお、ここで第1の対向電極の幅とは、サーミスタ素体2の両端面2d,2eを結ぶ方向と直交する方向の第1の対向電極の寸法をいうものとする。

【0032】これに対して、より好ましくは、サーミスタ層を介して重なり合う第1の対向電極の幅を異ならせることにより、得られる抵抗値のばらつきをより一層低減することができる。すなわち、図4(a)及び(b)に示すように、第1の対向電極5aの幅を、第1の対向電極5aとサーミスタ層を介して重なり合う第1の対向電極6aの幅よりも広くした場合、幅方向における積層ずれに起因する抵抗値のばらつきを低減することができる。すなわち、積層や対向電極5a、6aの印刷に際し、第1の対向電極6aが第1の対向電極5aを下方に投影した領域内に位置する限り、第1の対向電極5a、6a間の重なり面積が変動しないため、上記印刷ずれや積層ずれに起因する抵抗値のばらつきを防止することができる。

【0033】また、図5(a)に示すように、第1,第2の対向電極3a,3bの形成にあたり、セラミックグリーンシート9bの端縁に連なる部分において、セラミックグリーンシートの全幅に至る接続部3a₁,3b₁を設けてもよい。このように、接続部3a₁,3b₁を設けることにより、第1,第2の対向電極3a,3bの外部電極7,8との電気的接続の信頼性を高め得る。しかも、第1,第2の対向電極3a,3bの主要部分は、セラミックグリーンシート9bよりも幅が狭くされているため、耐湿性も高められる。

【0034】さらに、図5(b)に示すように、第1,第2の対向電極3a,3bが、先端側に互いに間挿し合う電極指3a2,3b2を有するくし歯状としてもよい。このように第1,第2の対向電極3a,3bをくし歯状に対向させることにより、より一層低抵抗化を図り得る。

【0035】次に、具体的な実験例に基づき、第1の実

施例のNTCサーミスタ素子によれば、低抵抗化を図った場合でも抵抗値のばらつきを低減し得ることを示す。サーミスタ素体2を構成するために、Mn,Ni,Coの酸化物を主体とする複数枚のセラミックグリーンシートを用意し、その上面に第1,第2の対向電極3a,3b~6a,6bをそれぞれ印刷してなるセラミックグリーンシートを作製した。第1,第2の対向電極が印刷されたセラミックグリーンシート9a~9d(図3)を積層し、さらに対向電極を印刷していない適宜の枚数のセラミックグリーンシート9aを上下に積層した。

【0036】上記のようにして得られた積層体を焼成し、得られたサーミスタ素体に、Agよりなる電極を塗布し、焼き付けることにより外部電極7,8を形成した。上記のようにして、第1の実施例のNTCサーミスタ素子を作製し、かつ第1,第2の対向電極からなる内

部電極の積層数を種々異ならせ、第1の実施例に従った NTCサーミスタ素子を種々作製した。また、このよう にして得られたNTCサーミスタ素子の抵抗値及び抵抗 ばらつきを評価した。結果を下記の表1に示す。

【0037】比較のために、上記実施例のNTCサーミスタ素子と同じ材料を用い、かつ同寸法の従来の対向型NTCサーミスタ素子67及び積層型NTCサーミスタ素子71を作製した。この従来の対向型NTCサーミスタ素子67及び積層型NTCサーミスタ素子71においても、内部電極の積層数を変化させ、種々の枚数の内部電極を有するものを作製し、かつ抵抗値及び抵抗ばらつきを評価した。結果を下記の表1に併せて示す。

[0038]

【表1】

	第1の実施例			比 較 例				
] 	第1の実	加 1991	対 向 型			積 層 型		
積層数	抵抗値R [kΩ]	抵抗 ばらつき R _{3CV} [約]	積層数	抵抗値R [kΩ]	抵抗 ばらつき R s c (- 1%)	積層数	抵抗値R [kΩ]	抵抗 ばらつき R sev[k]
2	1. 30	6	1	5. 8	7	2	1. 59	2 5
3	0.62	5	3	3. 6	6	3	0.78	1 8
4	0. 4 1	4	5	2. 5	5	4	0, 50	15
6	0.25	3. 6				5	0.32	15
9	0. 15	3. 4				10	0.16	1 5

【0039】表1から明らかなように、対向型NTCサーミスタ素子では、ギャップにより抵抗値が決定されるため、抵抗ばらつき R_{3CV} を小さくし得る。これに対して、積層型NTCサーミスタ素子では、内部電極の積層ずれ、印刷ずれ及びマザーのセラミックグリーンシートからの切断ずれ等の種々の要因により、抵抗ばらつき R_{3CV} が非常に大きいことがわかる。

【0040】また、表1から明らかなように、第1の実施例に従って作製されたNTCサーミスタ素子では、内部電極の積層数が同一であれば、対向型NTCサーミスタ素子に比べて抵抗値が非常に小さいNTCサーミスタ素子を提供し得ることがわかる。

【0041】なお、対向型NTCサーミスタ素子では、内部電極数を増大させることにより低抵抗化を図り得るものの、 $1 \, \mathrm{k} \, \Omega$ 以下と抵抗値を低めるには、かなりの数の内部電極を積層しなければならず、従って厚み寸法が増大することがわかる。

【0042】また、第1の実施例に係るNTCサーミスタ素子において、第1,第2の対向電極からなる内部電極の数を種々変化させて、抵抗値及び抵抗ばらつきRを測定した。結果を図6,図7に示す。

【0043】図6及び図7から明らかなように、内部電極の枚数を増大させることにより、本発明によれば抵抗

値を著しく低下させ得ることがわかる。従って、用途に応じて、第1,第2の対向電極を有する内部電極の数を増減することにより、所望の抵抗値を有する、特に低抵抗のNTCサーミスタ素子を高精度に製造し得ることがわかる。

【0044】第1の実施例のNTCサーミスタ素子1では、第1,第2の外部電極7,8の被り部7a,8aが、好ましくは、下方電位に接続される対向電極と厚み方向において重なり合わないように構成されており、それによって抵抗値のばらつきがより一層低減される。これを、図1及び図8を参照して、説明する。

【0045】NTCサーミスタ素子1において、第2の外部電極8の被り部8 aは、図1に示すように、他方電位に接続される第1の対向電極3 aと厚み方向において重なり合わないように配置されている。この構造において、被り部8 aの長さ1、すなわち第12の外部電極18の端面12 e 12 e 12 e 13 e 13 e 13 e 14 e 13 e 14 e 15 e 16 e 16 e 17 e 17 e 18 e 19 e 11 e 19 e 19

【0046】また、比較のために、図8に示すように、

被り部8aが第1の対向電極3aと厚み方向においてX=+0. 1mmの長さで重なり合っているNTCサーミスタ素子11を作製し、同様に、抵抗値R、抵抗ばらつき R_{3CV} を測定し、かつ抵抗変化率を評価した。結果を

表2に併せて示す。 【0047】 【表2】

L	抵抗值R	抵抗ばらつき	重なり長さX	抵抗変化率 ΔR
[1010]	[kΩ]	R _{3CV} [%]	(mm]	[%]
0.2	0.410	5	-0.2↑重	
0.3	0.410	5	- 0. 1 ら	0
0.4	0.409	5. 2	o ↓\\\\	-0.02
0. 5	0.403	7	+0.1 重 な る	-1.8

【0048】表2から明らかなように、図8に示したNTCサーミスタ素子11では、外部電極8の被り部8aが、他方電位に接続される第1の対向電極3aと厚み方向において重なり合っているため、抵抗値が重なり合っていない場合に比べて大きく変化することがわかる。言い換えれば、外部電極8の被り部8aが他方電位に接続される対向電極3aと厚み方向において重なり合っている場合、該被り部8aの長さ寸法がばらつくと抵抗値が大きくばらつくことがわかる。

【0049】従って、好ましくは、上記のように、外部電極8の被り部8aを、他方電位に接続される対向電極3aと厚み方向において重なり合わないように配置することにより、抵抗値R及び抵抗ばらつきR_{3CV} をより一層低減し得ることがわかる。

【0050】また、第1の実施例のNTCサーミスタ素子1では、外部電極8の被り部8aの先端 P_1 と、他方電位に接続される対向電極3aの先端 P_2 との間の距離が、抵抗値のばらつきに影響することを見出した。好ましくは、本発明においては、上記 P_1 , P_2 間の距離は、同一内部電極の第1の対向電極3aと第2の対向電極3bとの間のギャップの寸法gよりも大きくされ、それによって抵抗ばらつき R_{3CV} の低減を果たすことができる。

【0051】第1の実施例のNTCサーミスタ素子1において、ギャップの寸法gを0.25mmとし、第2の外部電極8の被り部8aの長さしを0.3mm、第2の対向電極3bの長さ寸法を0.05mmとし、対向電極3aとサーミスタ素体2の上面との間のサーミスタ層の厚み t(図1参照)を下記の表3に示すように変化させることにより P_1 , P_2 間の距離を変化させて、抵抗値のばらつきを評価した。結果を下記の表3に示す。

[0052]

【表3】

厚み t [.mm]	P ₁ とP ₂ との 距離p [mm]	抵抗 ばらつき R _{scv} [X]	
0.8	0. 28	4. 0	
0.75	0.255	4. 2	
0.70	0.230	5.8	
0.65	0.205	8. 1	

【0053】表3から明らかなように、 P_1 , P_2 間の距離が、ギャップの長さ寸法gよりも大きい場合、抵抗ばらつき R_{300} を小さくし得ることがわかる。

【0054】(第2の実施例)図9は、本発明の第2の 実施例に係るNTCサーミスタ素子を示す断面図であ る。

【0055】NTCサーミスタ素子31では、直方体状のサーミスタ素体2内に、4層の内部電極が構成されている。もっとも、厚み方向中央に位置する内部電極32,33は、それぞれ、第1,第2の外部電極7,8に接続されている。すなわち、図1に示したNTCサーミスタ素子1の第1,第2の対向電極4a,4b,5a,5bに代えて、上記内部電極32,33が用いられている。その他の点については、NTCサーミスタ素子1と同様であるため、同一部分については、同一の参照番号を付することにより、第1の実施例の説明を援用することにより省略する。

【0056】NTCサーミスタ素子31のように、全ての内部電極が第1,第2の対向電極で形成される必要は必ずしもなく、第1,第2の対向電極で構成される内部電極以外に、従来の積層型NTCサーミスタ素子の場合と同様に交互に第1または第2の外部電極に接続された内部電極を適宜の枚数組み合わせてもよい。

【0057】この場合においても、対向型NTCサーミスタ素子と同様に、ギャップgにより抵抗値のばらつきを高精度に抑制することができ、かつ第1の対向電極と他の高さ位置の第1の対向電極もしくは内部電極とにより構成される部分、並びに上記積層型NTCサーミスタ

部において積層数の増大により抵抗値の低減を図り得る。

【0058】従って、NTCサーミスタ素子31のように、第1,第2の対向電極と、積層型NTCサーミスタ素子の内部電極とを適宜組み合わせることができ、その組み合わせ方についても任意である。

【0059】もっとも、好ましくは、NTCサーミスタ素子31のように、厚み方向最外層に、第1,第2の対向電極3a,3b,6a,6bを配置することが望ましい。積層型NTCサーミスタ素子の内部電極と同様に構成されている内部電極32,33では、その先端と、他方電位に接続される外部電極8または7との間の距離により抵抗値のばらつきが生じるのに対し、対向型内部電極3a,3b,6a,6bでは、このような原因による抵抗値のばらつきが生じ難い。

【0060】(第3の実施例)図10は、本発明の第3 の実施例に係るNTCサーミスタ素子を示す断面図であ る。NTCサーミスタ素子41は、サーミスタ素体2内 に、2層の内部電極を配置した構成を有し、各内部電極 が、それぞれ第1,第2の対向電極を有する。すなわ ち、上方に第1の対向電極42a,第2の対向電極42 bが形成されており、下方に第1の対向電極43aと第 2の対向電極43bとが形成されている。また、第1の 外部電極7に対向電極42a, 43bが、第2の外部電 極8に対向電極42b,43aが接続されている。従っ て、第1の実施例のNTCサーミスタ素子と同様に、抵 抗ばらつきの低減を果たし得るだけでなく、第1の対向 電極42aと第1の対向電極43aとがサーミスタ層を 介して重なり合っているため、低抵抗化も果たし得る。 すなわち、NTCサーミスタ素子41は、本発明のNT Cサーミスタ素子の最も簡略化された例に相当するもの である。

[0061]

【発明の効果】請求項1に記載の発明によれば、少なくとも1つの内部電極がギャップを隔てて同一平面内で対向された第1,第2の対向電極を有し、第1の対向電極の少なくとも一部が、サーミスタ層を介して隔てられた異なる高さ位置の反対電位に接続される内部電極と厚み方向に重なり合うように配置されているため、従来の対向型NTCサーミスタ素子と同様に抵抗値のばらつきを低減し得るだけでなく、上記第1の対向電極と他の内部電極との重なりにより、従来の積層型NTCサーミスタ素子と同様に抵抗値の低減を図り得る。

【0062】従って、高精度に低抵抗のNTCサーミスタ素子を提供することが可能となり、かつ電極構造により抵抗値及びそのばらつきの低減を図ることが可能とされているため、同一のB定数のサーミスタ材料を用いて広い範囲の抵抗値を得ることができる。言い換えれば、同一の抵抗値用のNTCサーミスタ素子を供給することができ

るので、ユーザー側における回路設計上の自由度を効果的に高め得る。

【0063】請求項2に記載の発明によれば、第1,第 2の対向電極からなる内部電極が、複数層の内部電極の うち最上層と最下層の一方または両方に配置されている ので、他方電位に接続される外部電極との間の距離によ る抵抗値のばらつきが生じ難い。

【0064】請求項3に記載の発明によれば、全ての内部電極が、上記第1,第2の対向電極を有するように構成されているので、抵抗値のばらつきをより一層低減することが可能となる。

【0065】請求項4に記載の発明によれば、第1または第2の外部電極に接続された対向電極が、第2または第1の外部電極と厚み方向において重ならないように配置されているので、これらの間の距離による抵抗値のばらつきを低減することができ、より一層抵抗値のばらつきを低減することができる。

【0066】請求項5に記載の発明によれば、第1または第2の外部電極と、第2または第1の外部電極に接続された内部電極との間の距離が、該内部電極の第1,第2の対向電極間のギャップの大きさよりも大きくされているので、さらに抵抗値のばらつきを低減することが可能となる。

【0067】請求項6に記載の発明では、第1の対向電極の幅がサーミスタ層を介して隔てられた内部電極の幅と異ならされているため、製造工程における幅方向の積層ずれや電極の印刷ずれに起因する抵抗値のばらつきを効果的に低減することが可能となる。

【図面の簡単な説明】

【図1】本発明の第1の実施例に係るNTCサーミスタ素子を示す断面図。

【図2】第1の実施例のNTCサーミスタ素子の製造工程において用いられるセラミックグリーンシート及び電極形状を示す分解斜視図。

【図3】第1の実施例のNTCサーミスタ素子の製造工程において複数枚のセラミックグリーンシートを積層する工程を説明するための略図的斜視図。

【図4】(a)及び(b)は、対向電極の幅を異ならせた構造を説明するための各平面図。

【図5】(a)及び(b)は、対向電極の平面形状の変形例を説明するための各斜視図。

【図6】第1の実施例のNTCサーミスタ素子において、内部電極の積層数と抵抗値との関係を示す図。

【図7】第1の実施例のNTCサーミスタ素子において、内部電極の積層数と抵抗値のばらつきR_{3CV} との関係を示す図。

【図8】外部電極被り部が対向電極と厚み方向において 重なり合っている比較のために用意した構造を説明する ための断面図。

【図9】本発明の第2の実施例に係るNTCサーミスタ

素子を示す断面図。

【図10】本発明の第3の実施例に係るNTCサーミスタ素子を示す断面図。

【図11】従来の対向型NTCサーミスタ素子の一例を示す断面図。

【図12】従来の対向型NTCサーミスタ素子の他の例を示す断面図。

【図13】従来の積層型NTCサーミスタ素子を示す断面図。

【符号の説明】

1…NTCサーミスタ素子

2…サーミスタ素体

2a~2c…サーミスタ層

2 d, 2 e…端面

3a, 4a, 5a, 6a…第1の対向電極

3b, 4b, 5b, 6b…第2の対向電極

7,8…第1,第2の外部電極

7a,8a…外部電極の被り部

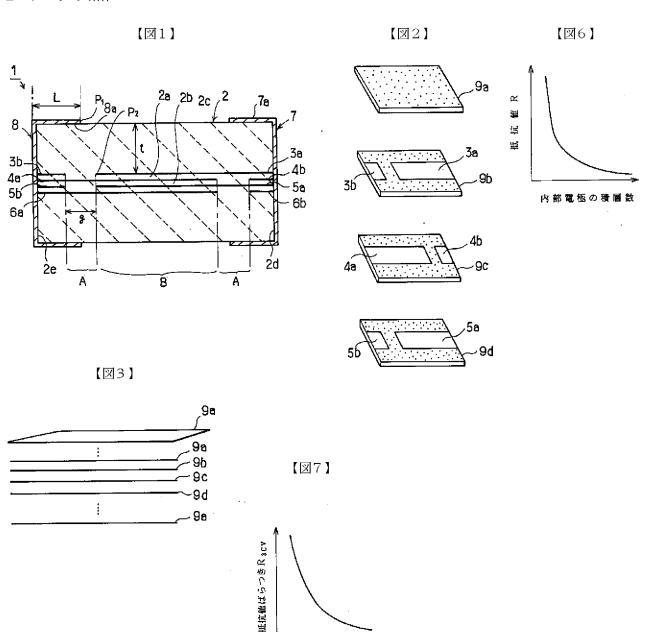
31…NTCサーミスタ素子

32,33…内部電極

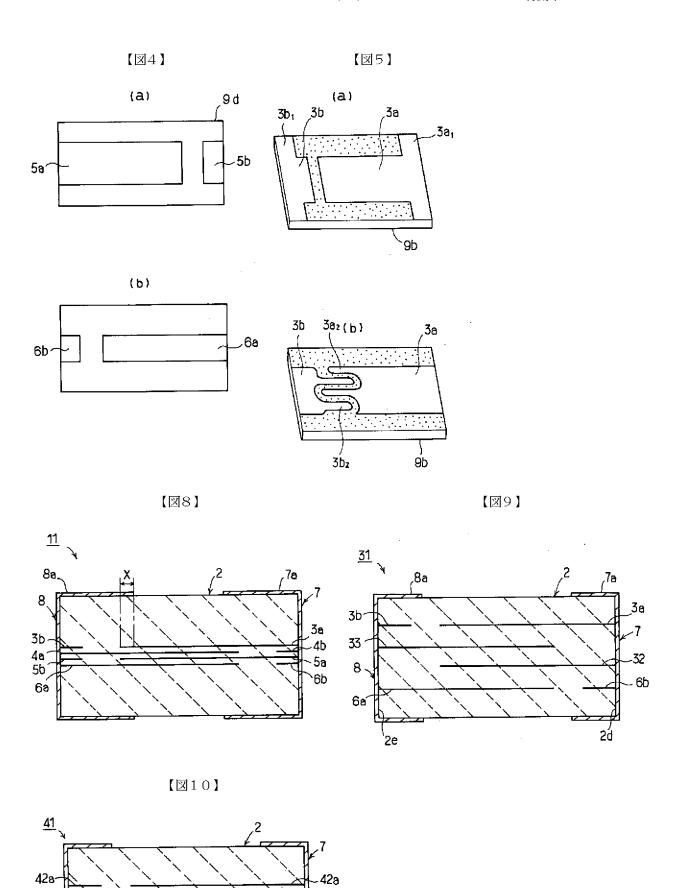
41…NTCサーミスタ素子

42a, 43a…第1の対向電極

42b, 43b…第2の対向電極



内部電極の積層数

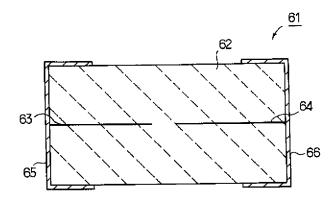


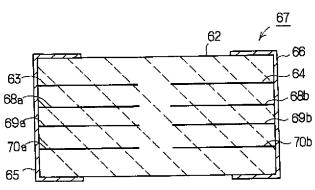
-43b

43á

【図11】

【図12】





【図13】

